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November 2013

# FQP20N06L

# N-Channel QFET<sup>®</sup> MOSFET 60 V, 21 A, 55 m $\Omega$

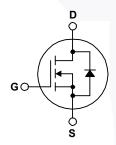
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### **Features**

- 21 A, 60 V,  $R_{DS(on)}$  = 55 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 10.5 A
- Low Gate Charge (Typ. 9.5 nC)
- Low Crss (Typ. 35 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP20N06L	Unit
$V_{DSS}$	Drain-Source Voltage		60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	21	Α
	- Continuous (T <sub>C</sub> = 100	°C)	14.7	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	84	Α
$V_{GSS}$	Gate-Source Voltage		± 20	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	170	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	21	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	5.3	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		53	W
	- Derate above 25°C		0.35	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Ran	ge	-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

## **Thermal Characteristics**

Symbol	Parameter	FQP20N06L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.85	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP20N06L	FQP20N06L	TO-220	Tube	N/A	N/A	50 units

### **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.06		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate voltage Drain Current	V <sub>DS</sub> = 48 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA

## **On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.5	V
R <sub>DS(on)</sub>	Static Drain-Source	$V_{GS} = 10 \text{ V}, I_D = 10.5 \text{ A}$		0.042	0.055	0
, ,	On-Resistance	$V_{GS} = 5 V, I_D = 10.5 A$		0.055	0.07	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 10.5 A		11		S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,	 480	630	pF
Coss	Output Capacitance	f = 1.0 MHz	 175	230	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		 35	45	pF

# **Switching Characteristics**

	0					
$t_{d(on)}$	Turn-On Delay Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 10.5 A,		10	30	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		165	340	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1.0 -1 -1		35	80	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	70	150	ns
$Q_g$	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 21 A,		9.5	13	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 5 V		2.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		5.5		nC

## **Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current		 	21	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		 	84	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 21 A	 	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 21 A,	 54		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs	 75		nC

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 450  $\mu$ H, I<sub>AS</sub> = 21 A, V<sub>DD</sub> = 25 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  21 A, di/dt  $\leq$  300 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature.

# **Typical Characteristics**

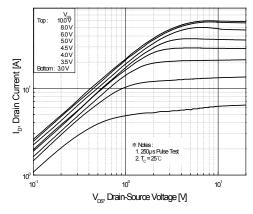


Figure 1. On-Region Characteristics

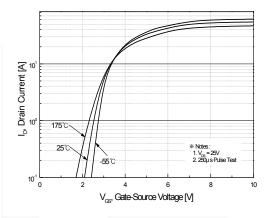


Figure 2. Transfer Characteristics

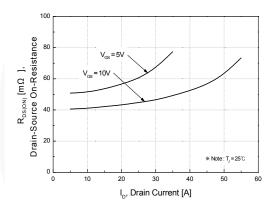


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

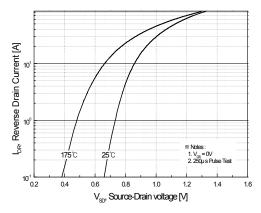


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

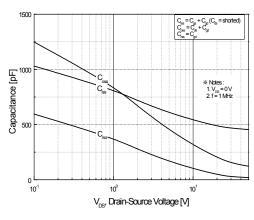


Figure 5. Capacitance Characteristics

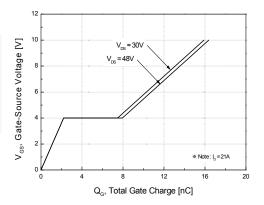


Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)

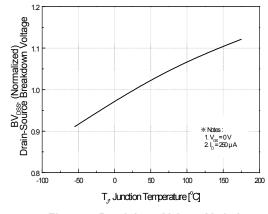


Figure 7. Breakdown Voltage Variation vs. Temperature

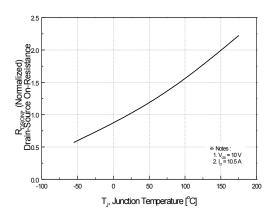


Figure 8. On-Resistance Variation vs. Temperature

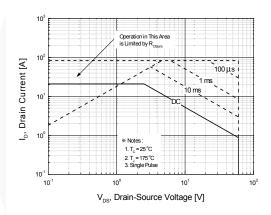


Figure 9. Maximum Safe Operating Area

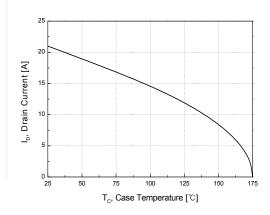


Figure 10. Maximum Drain Current vs. Case Temperature

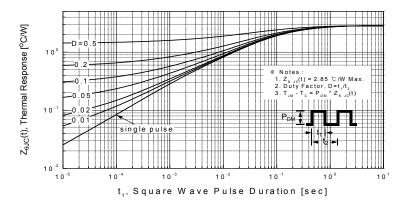


Figure 11. Transient Thermal Response Curve

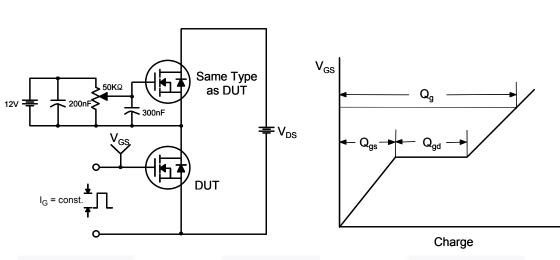


Figure 12. Gate Charge Test Circuit & Waveform

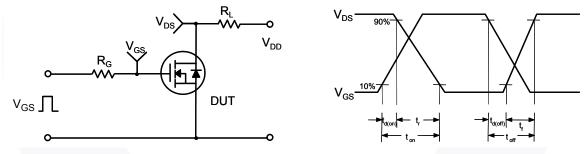


Figure 13. Resistive Switching Test Circuit & Waveforms

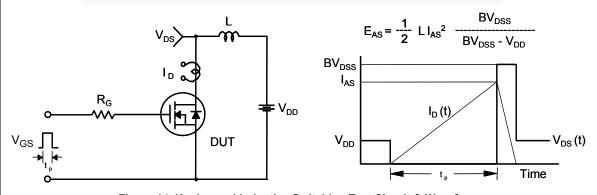
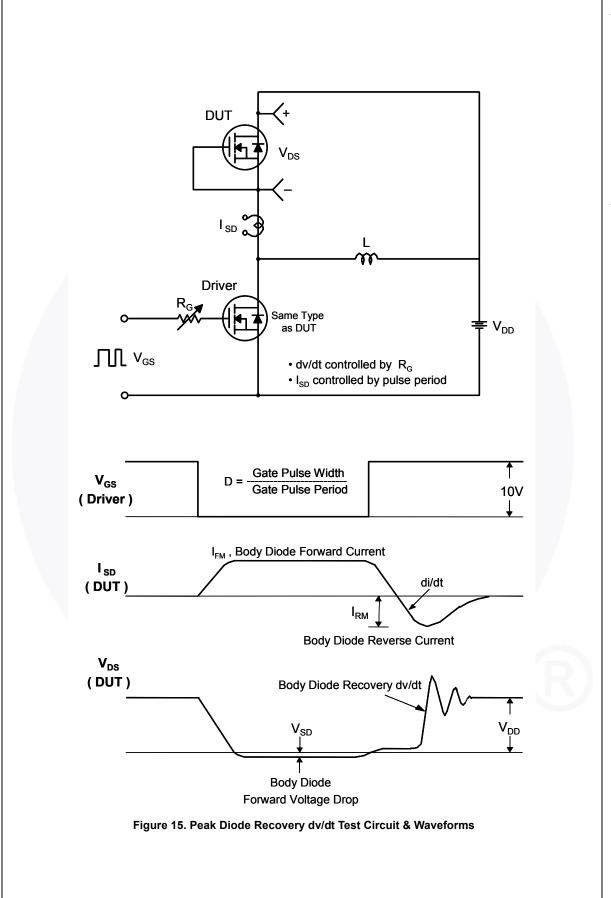
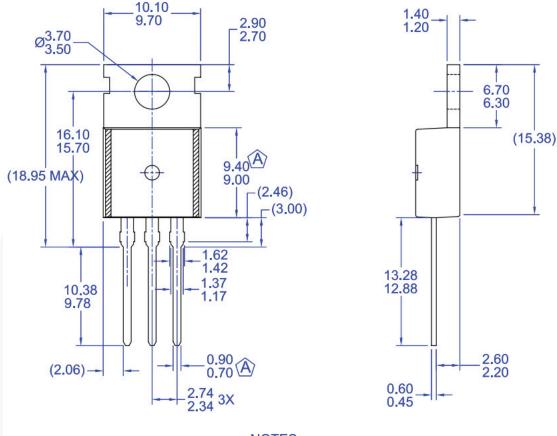


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**



4.70 4.30 10.20 9.80

### NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

### Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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